



# BUK964R7-80E

## N-channel TrenchMOS logic level FET

13 March 2014

Product data sheet

### 1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{gst(th)}$  rating of greater than 0.5V at 175 °C

### 3. Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$		-	-	80	V
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	[1]	-	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>		-	-	324	W
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>		-	3.6	4.7	mΩ
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	28.9	-	nC

[1] Continuous current is limited by package.

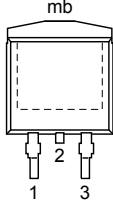
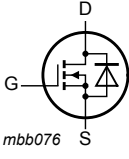


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK964R7-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK964R7-80E	BUK964R7-80E

## 8. Limiting values

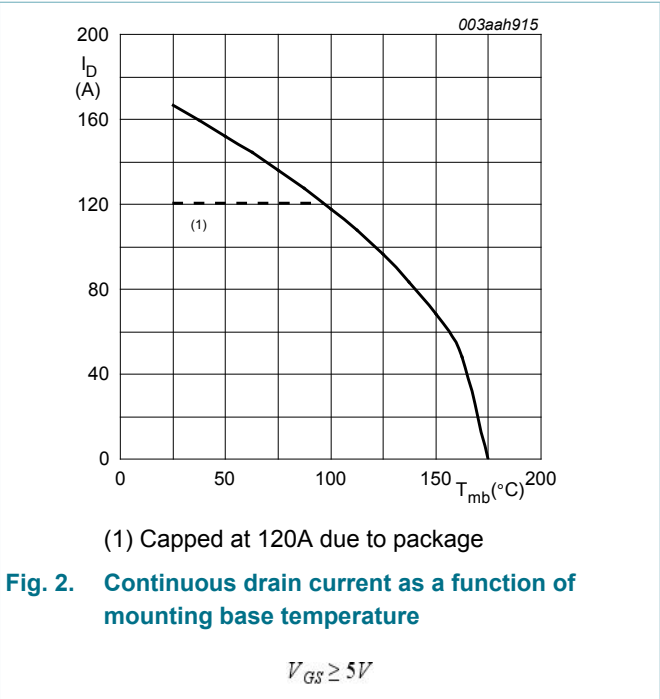
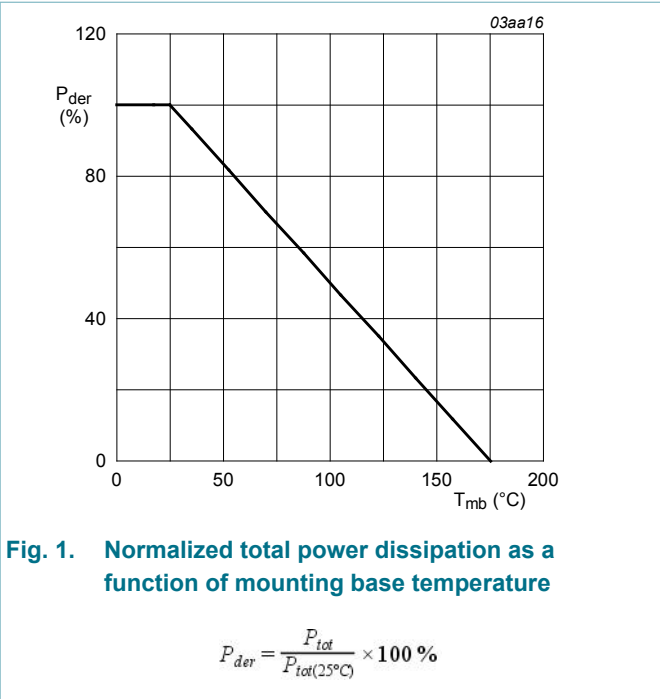
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$		-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	80	V
$V_{GS}$	gate-source voltage	$T_j \leq 175\text{ }^{\circ}\text{C}$ ; Pulsed	[1][2]	-15	15	V
		$T_j \leq 175\text{ }^{\circ}\text{C}$ ; DC		-10	10	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 1		-	324	W
$I_D$	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2	[3]	-	120	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2	[3]	-	120	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; Fig. 3		-	667	A
$T_{stg}$	storage temperature			-55	175	$^{\circ}\text{C}$

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	667	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 4	[4][5]	-	384	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>j</sub> and or V<sub>GS</sub>
- [3] Continuous current is limited by package.
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [5] Refer to application note AN10273 for further information.



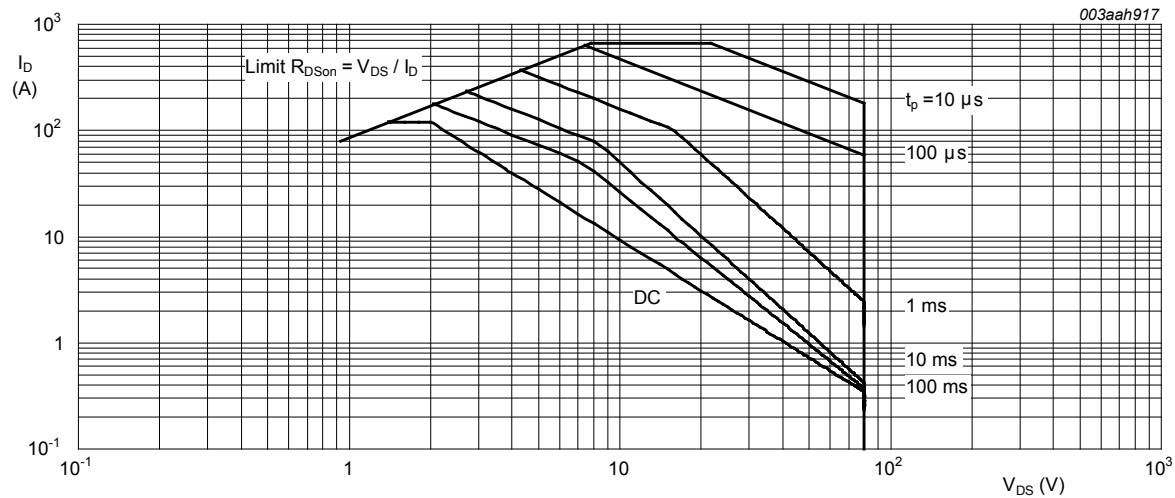


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

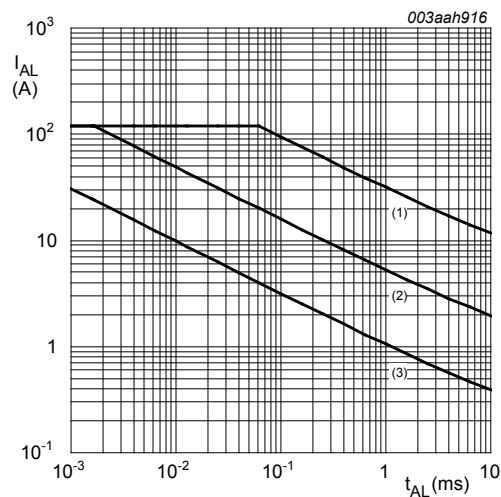


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j (mt)} = 25^{\circ}C$ ; (2)  $T_{j (mt)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.46	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

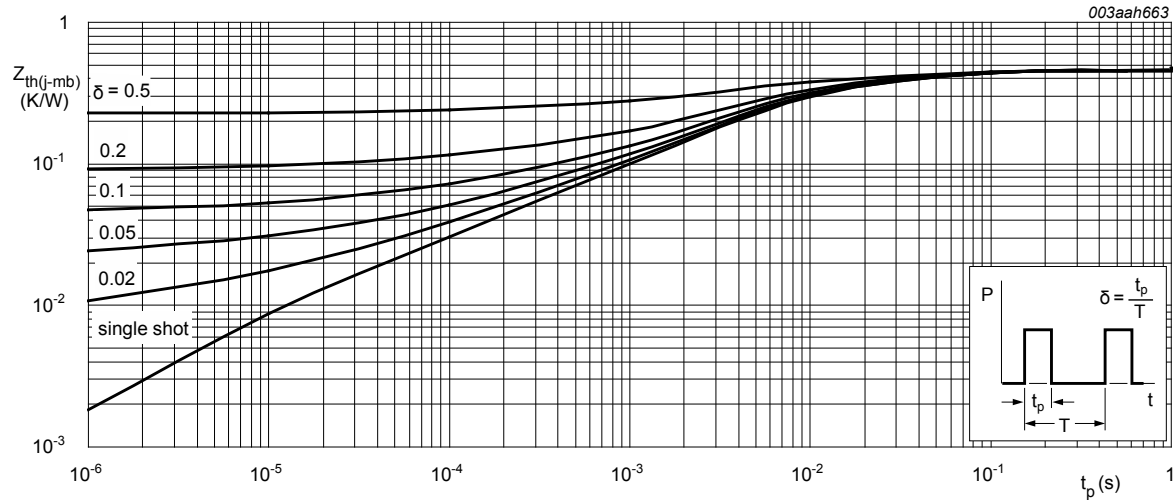


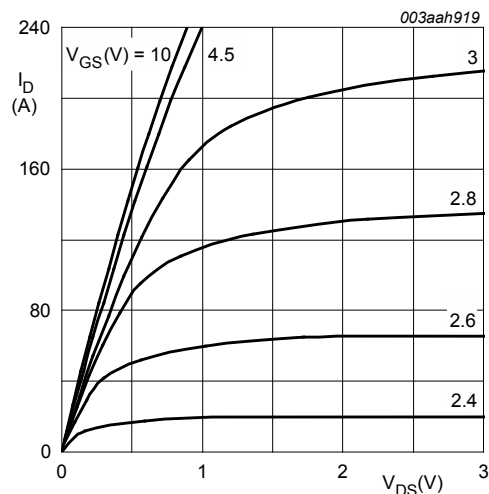
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

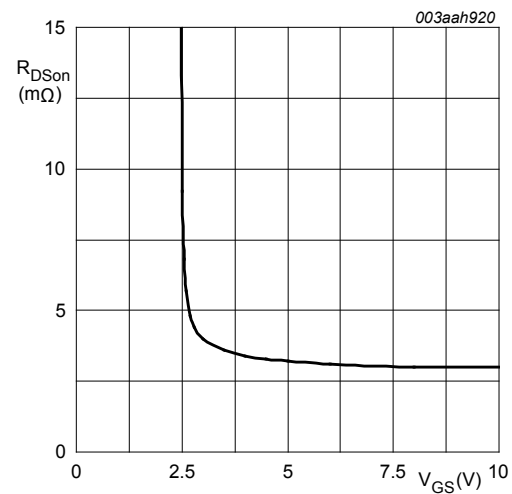
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		80	-	-	V
		$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ }^\circ\text{C}$		72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>		1.4	1.7	2.1	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	2.45	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>		0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 80\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	0.13	1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 175\text{ }^\circ\text{C}$		-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
		$V_{GS} = -10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	3.6	4.7	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	3.3	4.5	m $\Omega$
		$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 11</a>		-	-	11.7	m $\Omega$
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	92.1	-	nC
$Q_{GS}$	gate-source charge			-	25.7	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{GD}$	gate-drain charge		-	28.9	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_J = 25\text{ }^{\circ}\text{C}$ ; Fig. 15	-	11500	15340	pF
$C_{oss}$	output capacitance		-	744	892	pF
$C_{rss}$	reverse transfer capacitance		-	360	493	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 60\text{ V}$ ; $R_L = 2.4\text{ }\Omega$ ; $V_{GS} = 5\text{ V}$ ; $R_{G(ext)} = 5\text{ }\Omega$	-	54.2	-	ns
$t_r$	rise time		-	95.7	-	ns
$t_{d(off)}$	turn-off delay time		-	112	-	ns
$t_f$	fall time		-	82.3	-	ns
$L_D$	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
$L_S$	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^{\circ}\text{C}$ ; Fig. 16	-	0.77	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$	-	49.8	-	ns
$Q_r$	recovered charge		-	97.2	-	nC



$T_J = 25\text{ }^{\circ}\text{C}$ ;  $t_p = 300\text{ }\mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_J = 25\text{ }^{\circ}\text{C}$ ;  $I_D = 25\text{ A}$

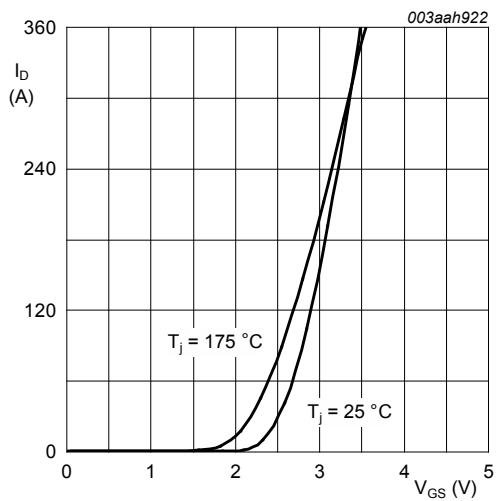


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{ V}$

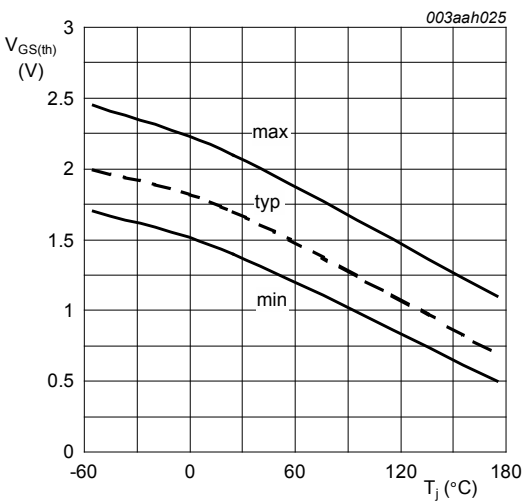


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

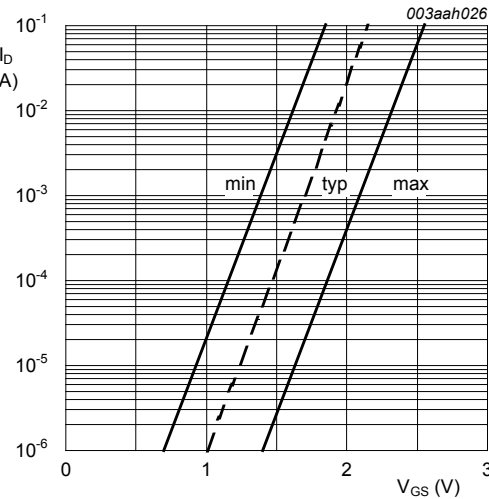


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

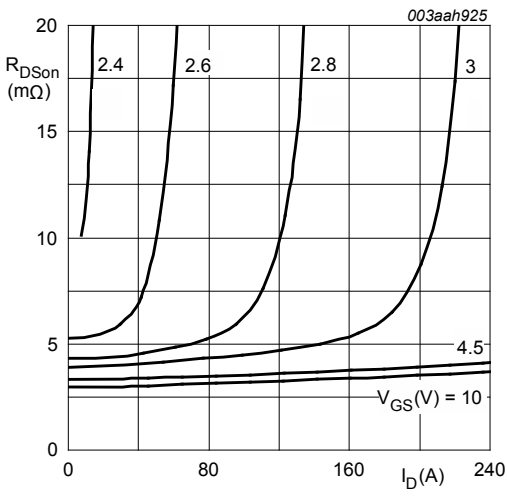


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\text{ }^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

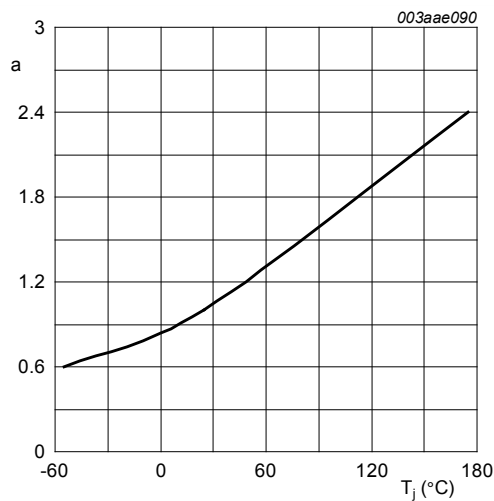


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)25^{\circ}\text{C}}}$$

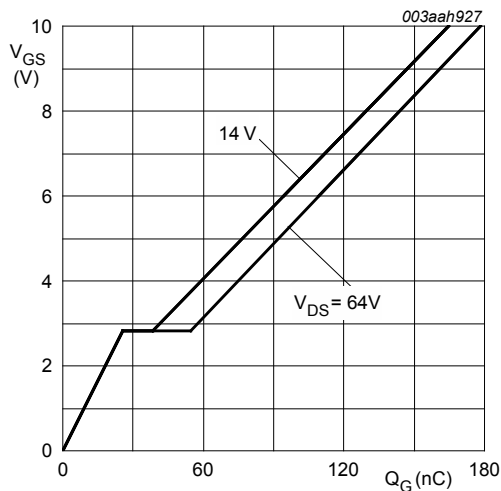


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 25\text{ A}$$

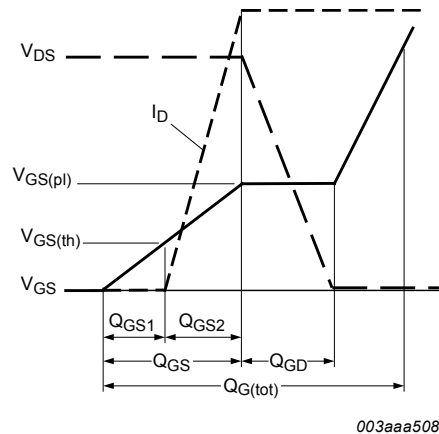


Fig. 13. Gate charge waveform definitions

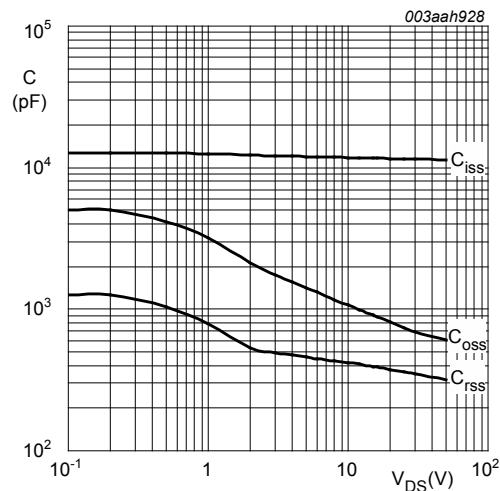


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$



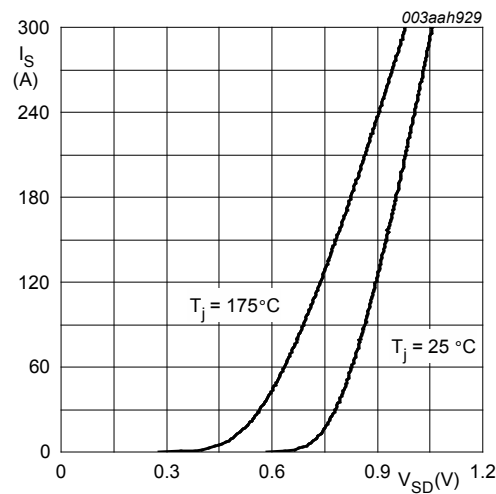


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

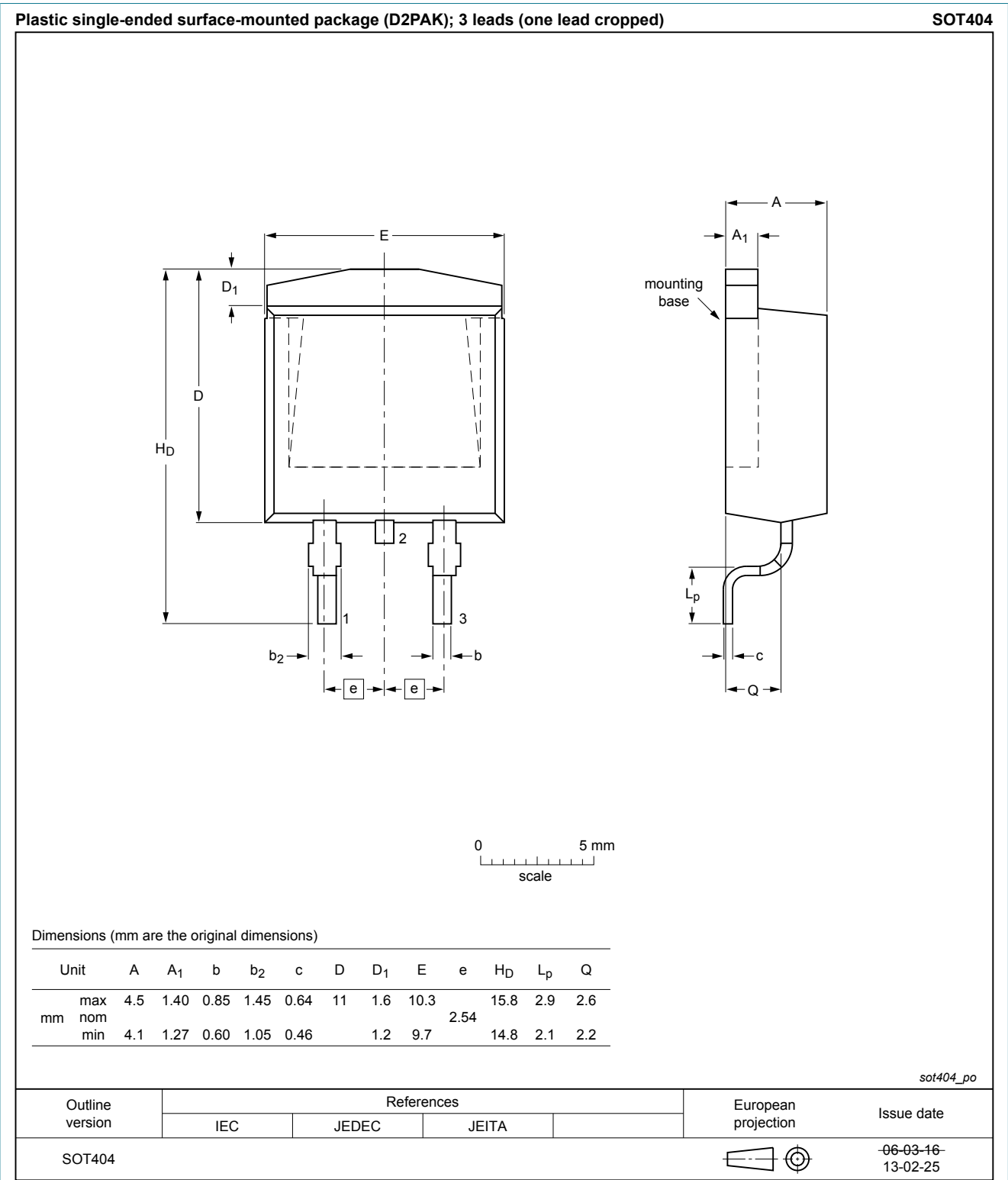


Fig. 17. Package outline D2PAK (SOT404)

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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